



AH& & H&

YU Y

D X WG U

WU

V YAU FU

DUU YY	X	G V	JU Y	I



YW W U UWY W

DUU YY	X	G V	JU Y			I
			A	H	AU	
	°C					
	°C					
	°C					
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H Y U U UWY W

DUU YY	X	G V	JU Y			I
			A	H	AU	

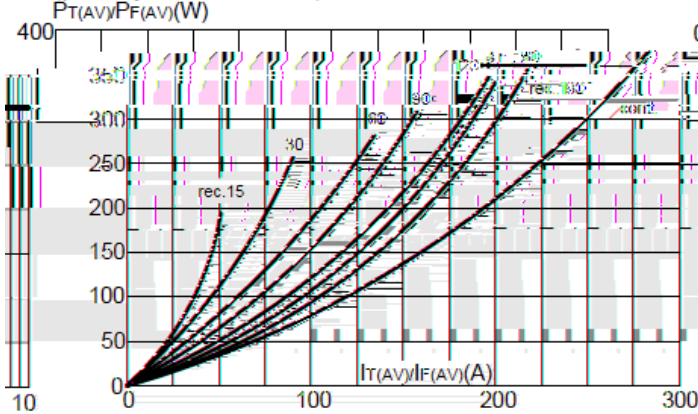
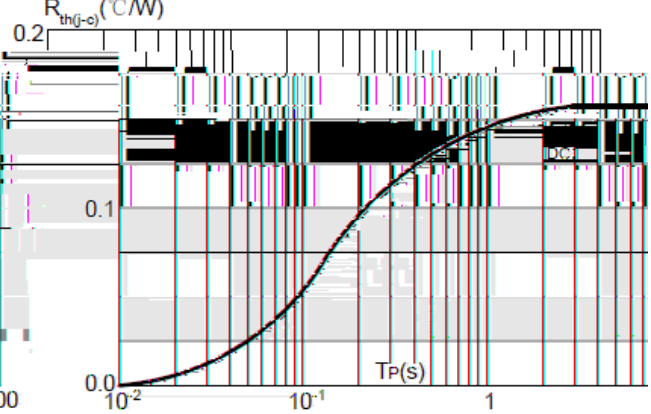
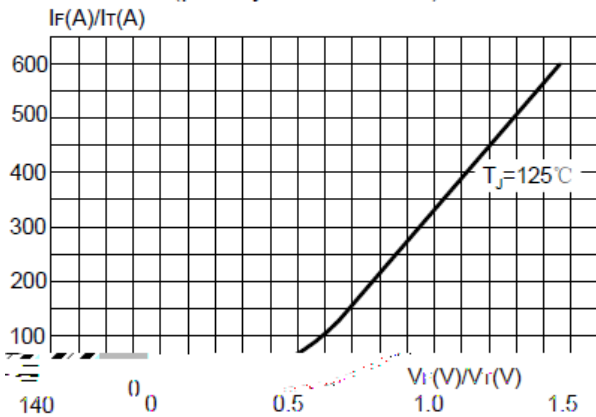
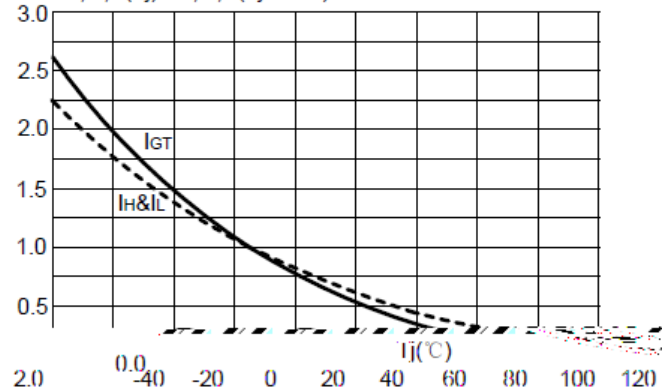
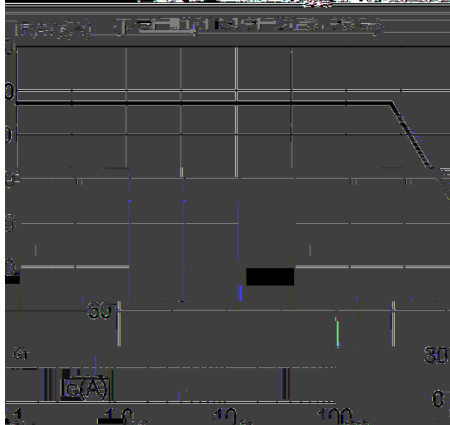
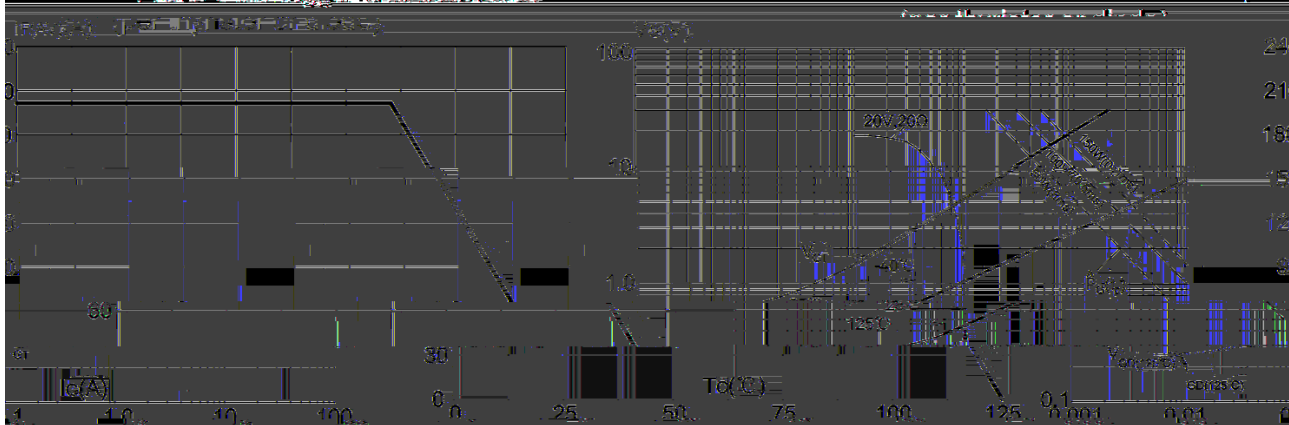


C XY

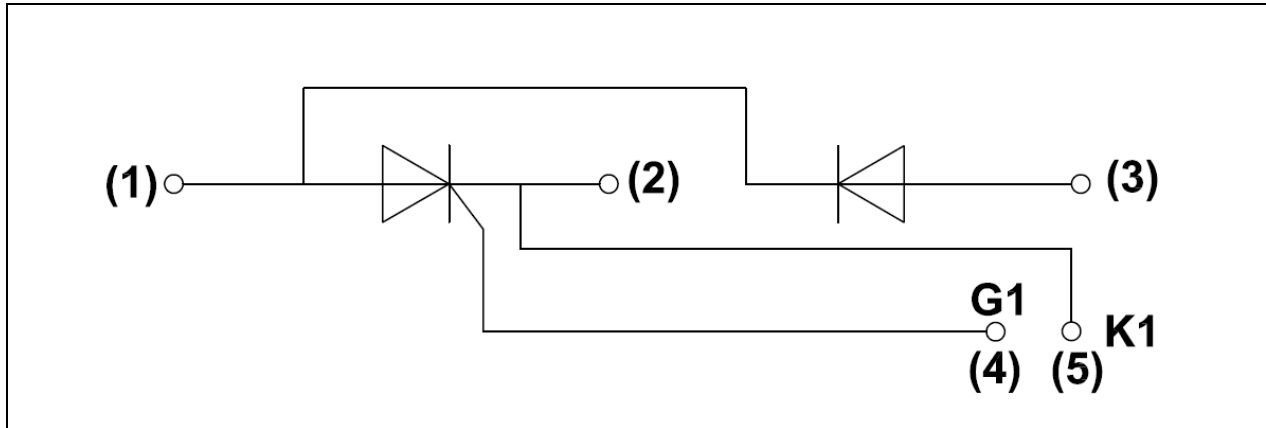
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Y W	AU	DWU Y	K Y	Y	DY U

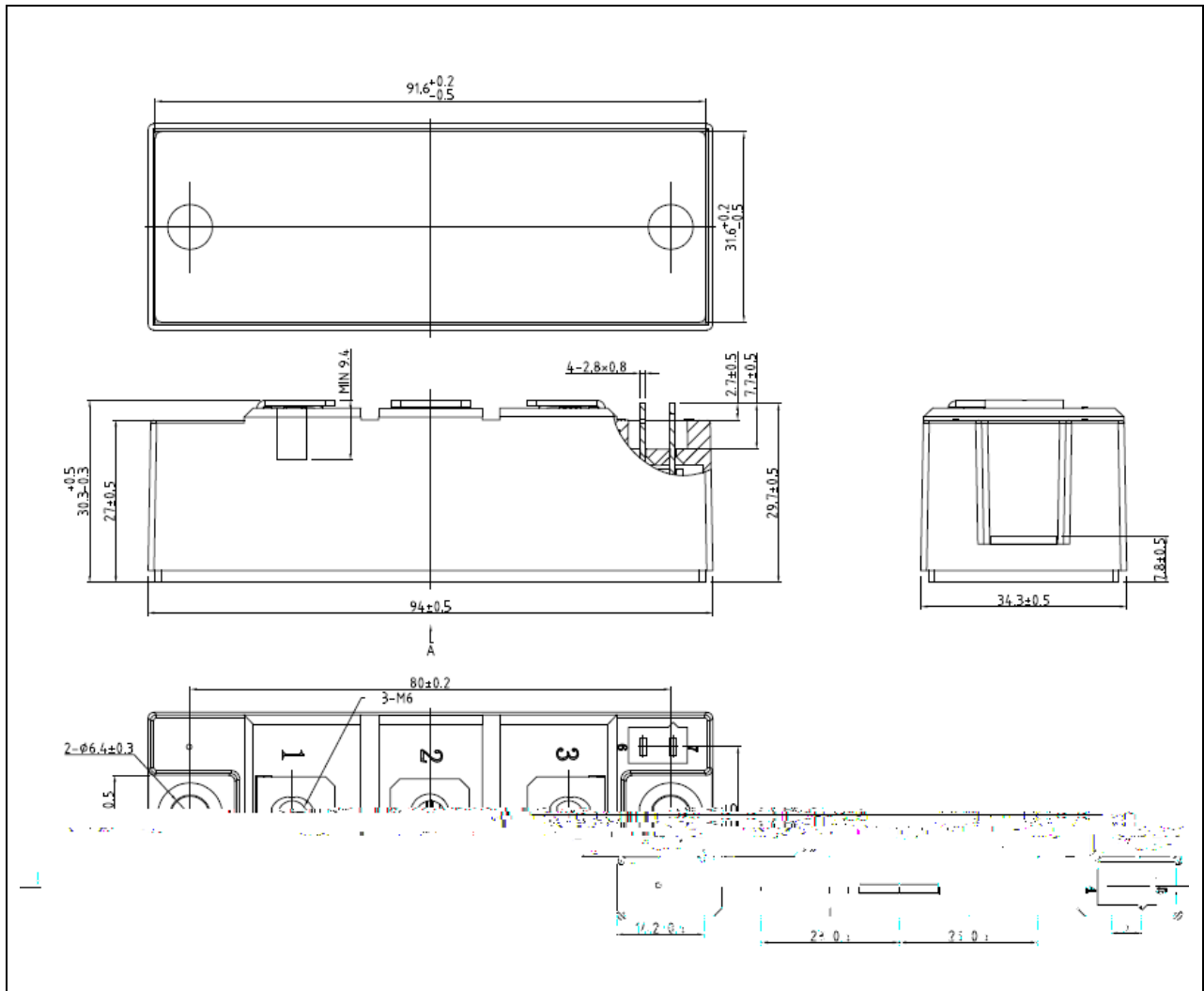
H W YW W H Y U U WY W

FIG.1:Power dissipation vs. on-state current
(per thyristor or diode)**FIG.2:** Maximum transient thermal impedance
junction to case(per thyristor or diode)**FIG.3:**Forward characteristics
(per thyristor or diode)**FIG.4:** Relative variations of gate trigger current, holding current and latching current versus junction temperature
 $I_{GT}, I_H, I_L(T_J)/I_{GT}, I_H, I_L(T_J=25^\circ\text{C})$ **FIG 5:** Gate trigger characteristics**FIG 6:** Forward current vs. case temperature

W U U



DUWU YC Y





AH& & H&

